

General Description

The WST2N7002A is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent $R_{DS(on)}$ and gate charge for most of the small power switching and load switch applications.

The WST2N7002A meet the RoHS and Green Product requirement with full function reliability approved.

Features

- High-speed switching
- Green Device Available

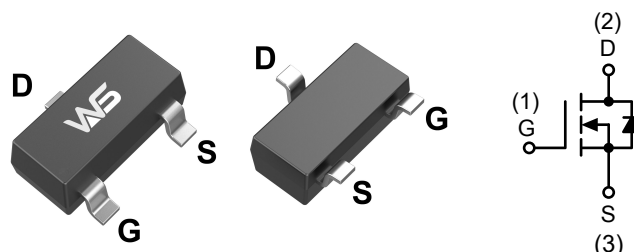
Product Summary

BV_{DSS}	$R_{DS(on)}$	I_D
60V	140mΩ	0.7A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC
- Networking DC-DC Power System

SOT-23L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	0.7	A
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	0.35	A
I_{DM}	Pulsed Drain Current ²	2.0	A
$P_D @ T_A = 25^\circ\text{C}$	Total Power Dissipation ³	0.25	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	625	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	0.05	---	$V/^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=0.5A$	---	140	450	m Ω
		$V_{GS}=4.5V$, $I_D=0.2A$	---	180	765	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	0.5	2	3.0	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-3.7	---	$mV/^{\circ}\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=60V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=60V$, $V_{GS}=0V$, $T_J=55^{\circ}\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 10	μA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=0.3A$	---	300	---	mS
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=30V$, $V_{GS}=10V$, $R_G=3.3\Omega$, $I_D=0.5A$	---	6	9.5	ns
T_r	Rise Time		---	8.2	10	
$T_{d(off)}$	Turn-Off Delay Time		---	10	13.6	
T_f	Fall Time		---	28	35	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1MHz$	---	130	350	pF
C_{oss}	Output Capacitance		---	70	120	
C_{rss}	Reverse Transfer Capacitance		---	25	36	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	0.7	A
I_{SM}	Pulsed Source Current ^{2,4}		---	---	2.0	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^{\circ}\text{C}$	---	---	1	V

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

3.The power dissipation is limited by 150°C junction temperature.

4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

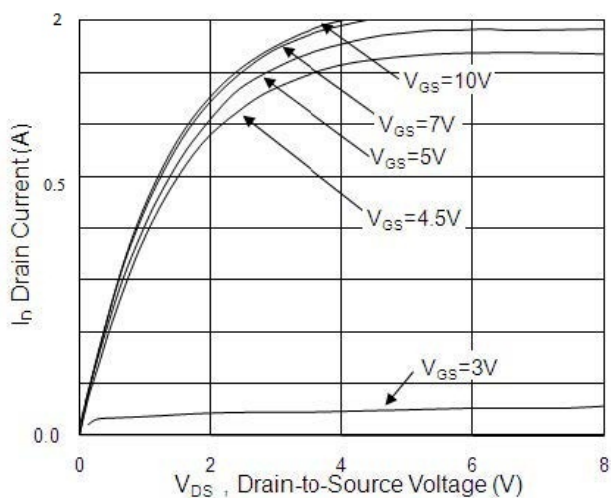


Fig.1 Typical Output Characteristics

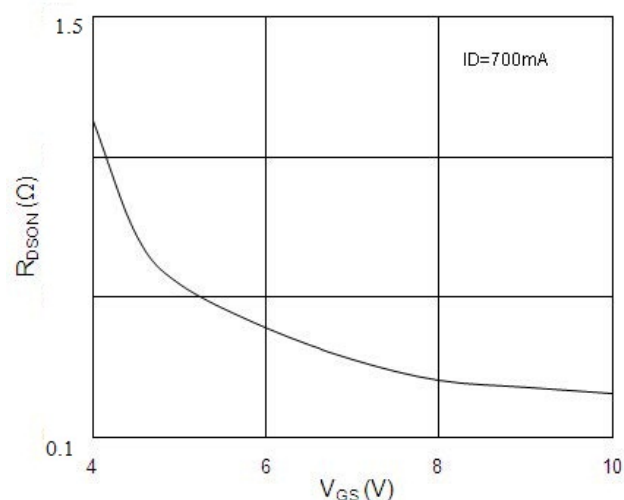


Fig.2 On-Resistance vs. Gate-Source Voltage

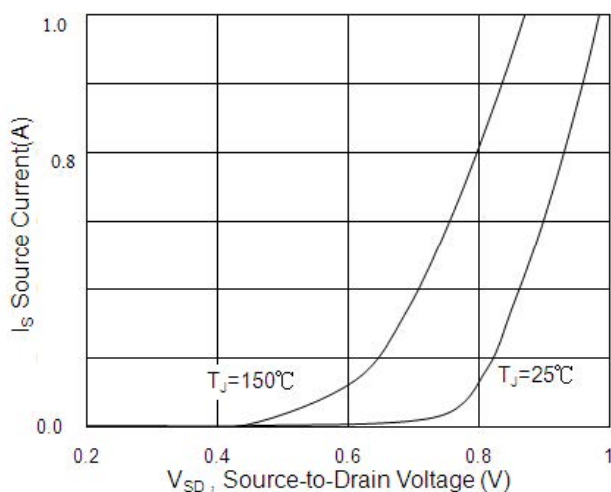


Fig.3 Forward Characteristics of Reverse

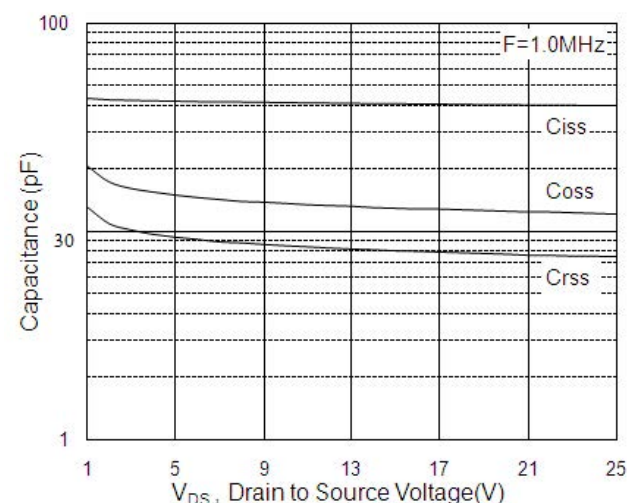


Fig.4 Capacitance

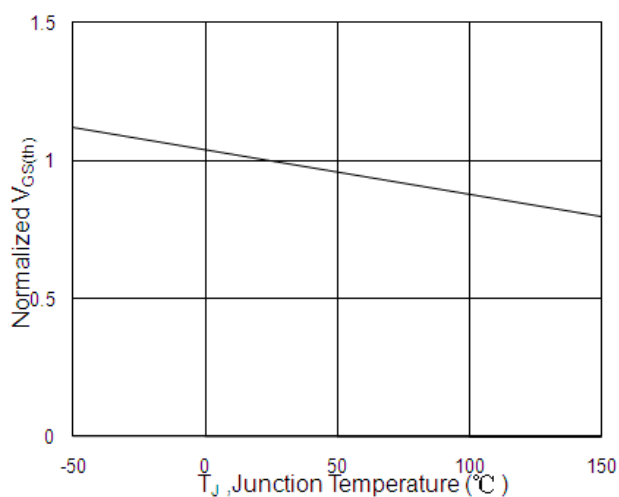


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

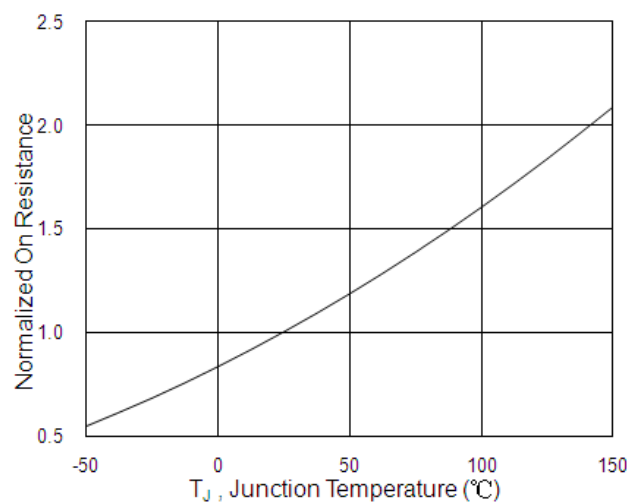


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

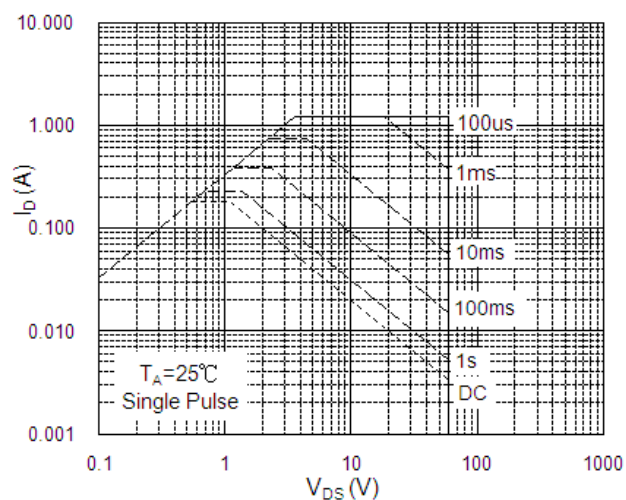


Fig.8 Safe Operating Area

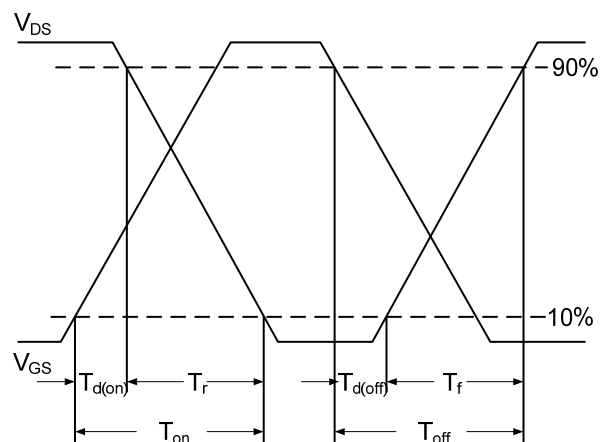


Fig.10 Switching Time Waveform

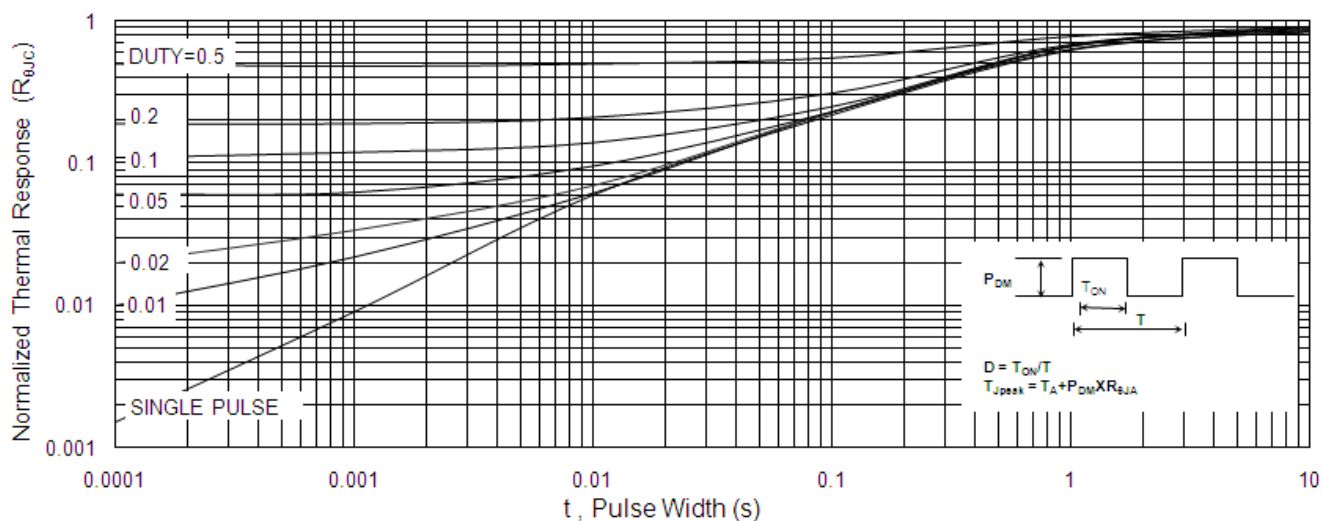
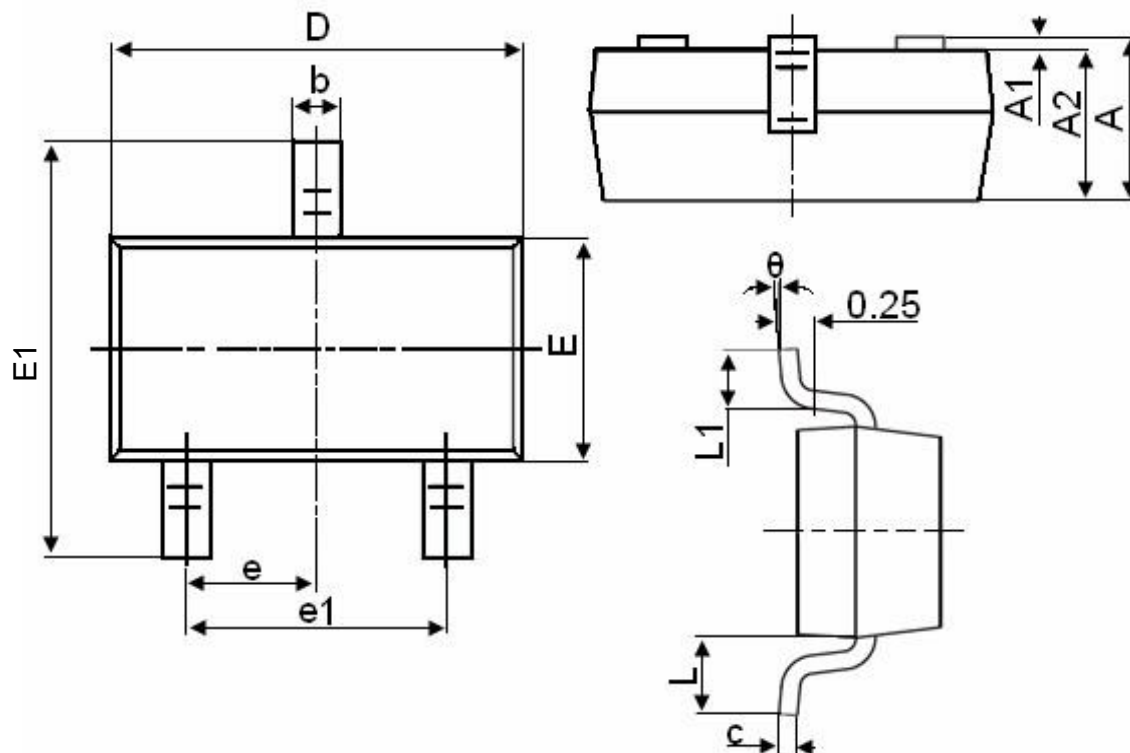


Fig.9 Normalized Maximum Transient Thermal Impedance

Packaging information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

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